

Shot noise in nanostructures - I

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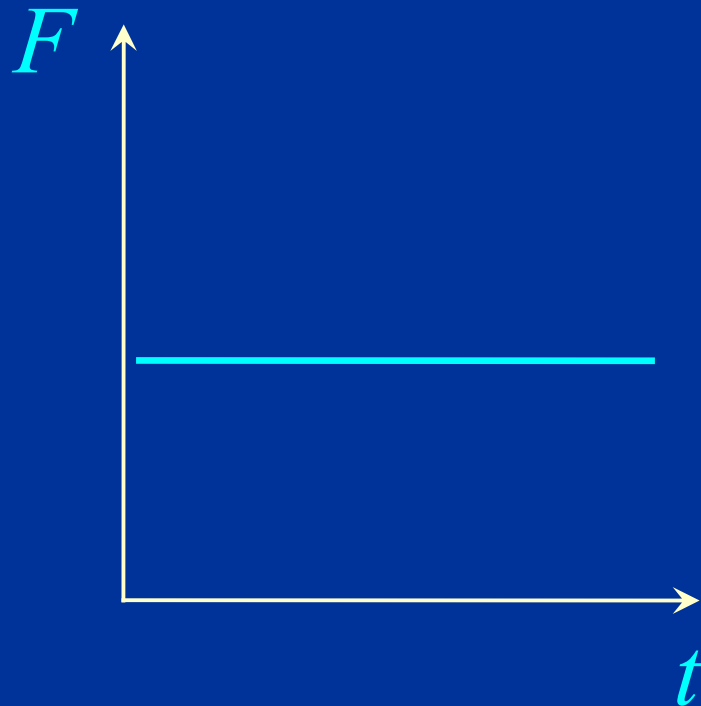
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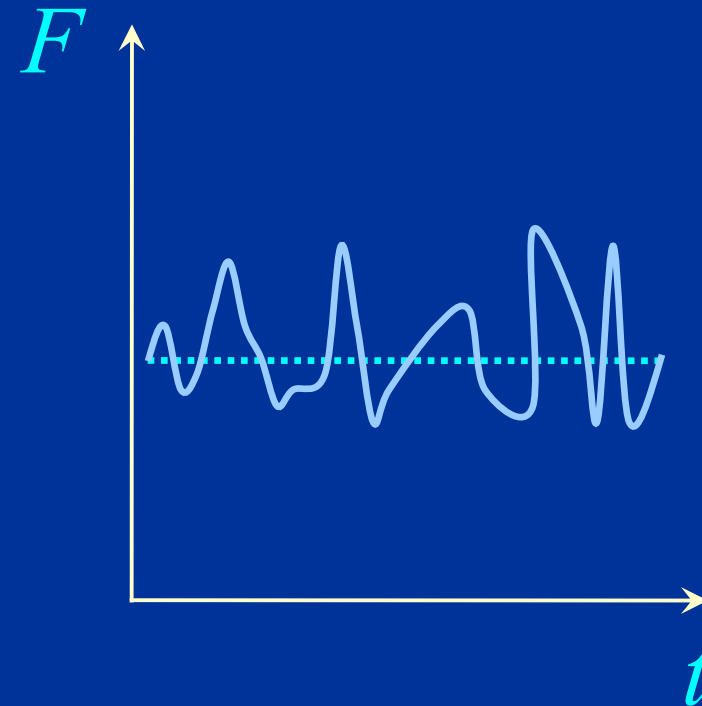
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Alexander Mirlin
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Signal and Noise

Expected:



Observed:



Irreproducible!!

Each new measurement yields a different pattern

Signal and Noise

Two approaches to noise:

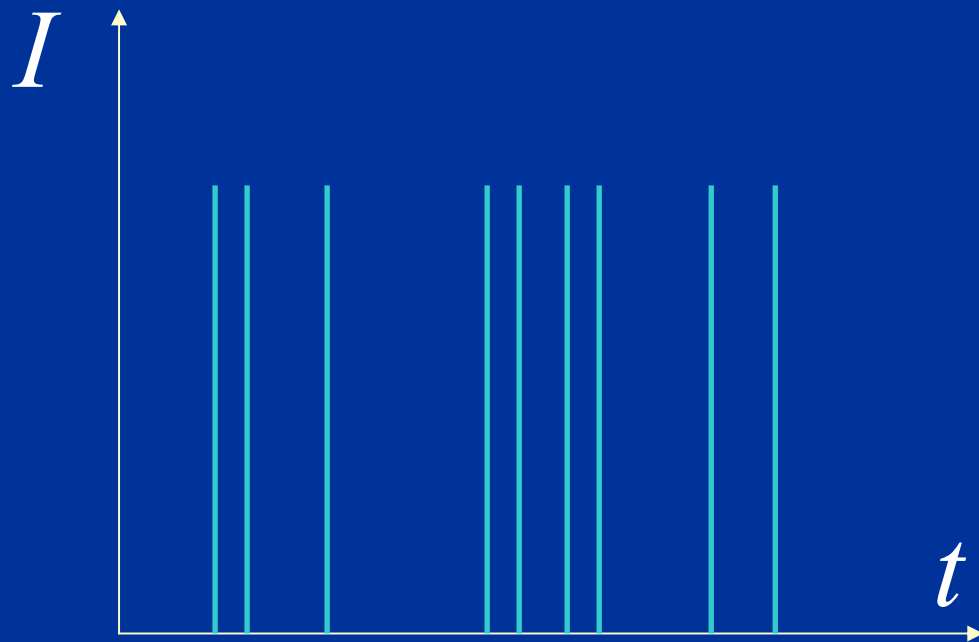
- Get rid of the noise and get the signal;
- Try to extract useful information from noise:
 - ❖ What is the magnitude of the fluctuations?
 - ❖ How are they correlated in time?

What information can we extract (Current noise):

- ❖ Transmission properties (“fingerprints”);
- ❖ Energy scales and transition rates.

Shot Noise

Schottky '18

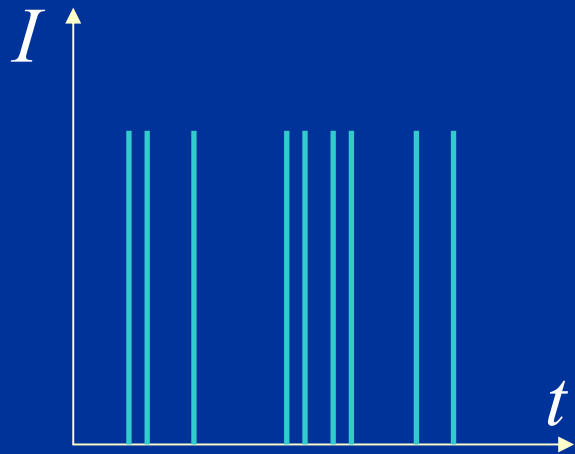


$$I = e \sum_n \delta(t - t_n)$$

Electric current as a sequence of random uncorrelated events

Shot Noise – Poisson statistics

Schottky '18



$$I = e \sum_n \delta(t - t_n)$$

τ - average time between the events

Average current: $\langle I \rangle = e / \tau$

Noise: $S(\omega) = 2 \langle I(t)I(t') \rangle_\omega = 2e^2 / \tau = 2e \langle I \rangle$

Higher moments -> full counting statistics

Landauer formula

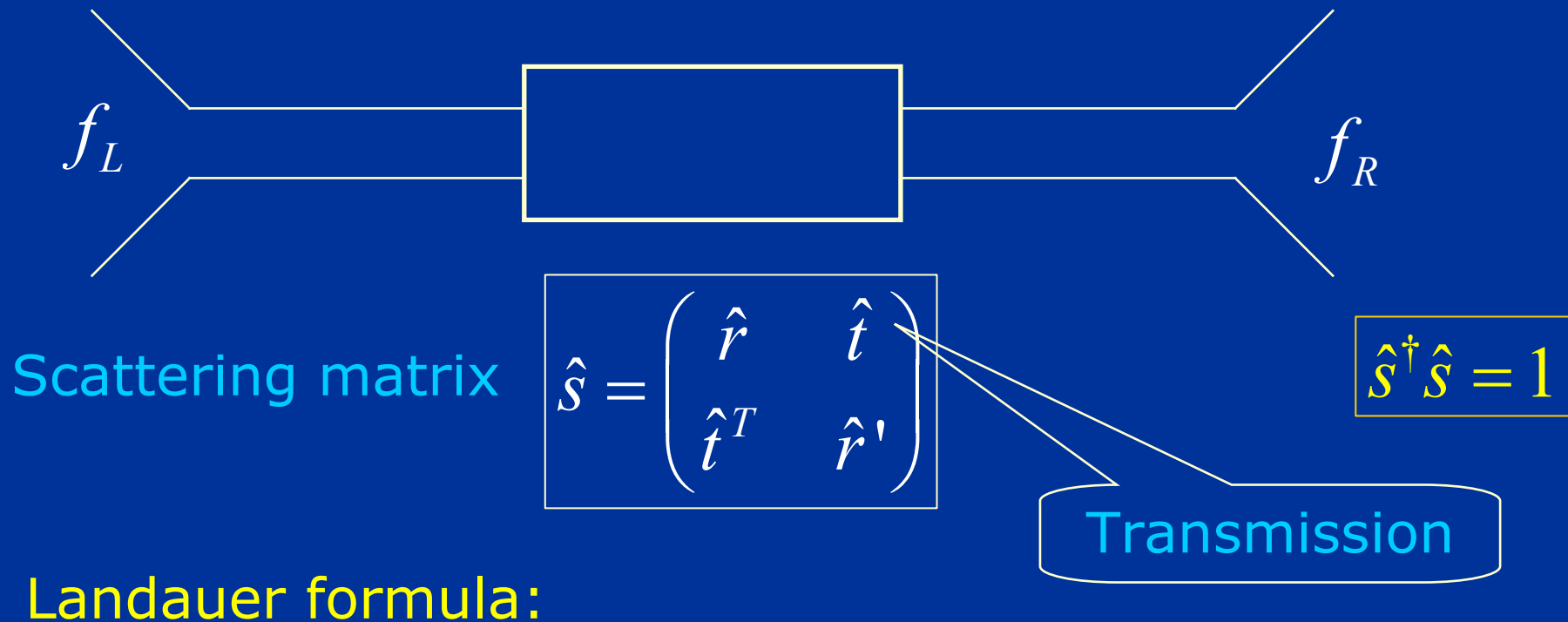


Scattering theory of transport

Input: Scattering properties of a nanostructure
(from quantum mechanics)

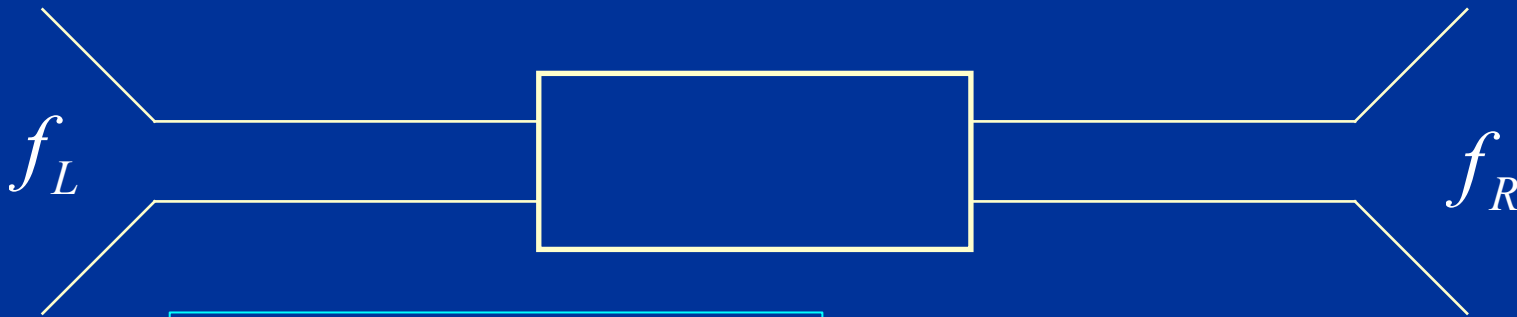
Output: Transport properties

Landauer formula



$$I = 2_s \frac{e}{2\pi\hbar} \int dE \text{Tr} \hat{t}^\dagger \hat{t} (f_L(E) - f_R(E)) = 2_s \frac{e^2}{2\pi\hbar} \sum_p T_p V$$

Shot noise



Noise: $S = 2 \langle I(t)I(t') \rangle_{\omega=0}$

$$S = 2_s \frac{e^3}{\pi \hbar} \sum_p \int dE \left\{ T_p [f_L(1-f_L) + f_R(1-f_R)] + T_p(1-T_p)(f_L - f_R)^2 \right\}$$

Does not look like Poisson value?

Nyquist-Johnson noise

Equilibrium: $f_L = f_R$

$$S = 2_S \frac{2e^2}{\pi\hbar} k_B T \sum_p T_p$$

Nyquist-Johnson noise

Fluctuation-dissipation theorem: Equilibrium fluctuations are related to the linear response

$$S = 4k_B T G$$

Zero-temperature shot noise

$$S = 2_S \frac{e^3}{\pi \hbar} |V| \sum_p T_p (1 - T_p)$$

Shot noise

Khlos '87

Lesovik '89

Büttiker '90

Compare to the Poisson value:

$$S < S_P$$

$$S_P = 2eI = 2_S \frac{e^3}{\pi \hbar} |V| \sum_p T_p$$

(Tunnel junction: $S = S_P$)

Shot noise suppression due to statistical correlations!

Fano factor:

$$F = \frac{S}{S_P} = \frac{\sum T_p (1 - T_p)}{\sum T_p} \leq 1$$

Noise in nanostructures

- Shot noise: white, contains information on transmission properties.
- Nyquist-Johnson noise: white, only at finite temperature, contains the same information as the conductance.
- $1/f$ noise: always present in the experiment.
Origin: sample-specific.
Information: unclear.
To avoid: high-frequency measurements.

Shot noise

Shot noise

Non-interacting electrons:

- ❖ $T(1-T)$
- ❖ Multi-terminal conductors
- ❖ Counting statistics

Interacting electrons:

- ❖ Perturbation theory
- ❖ Non-linear transport
- ❖ Strongly correlated

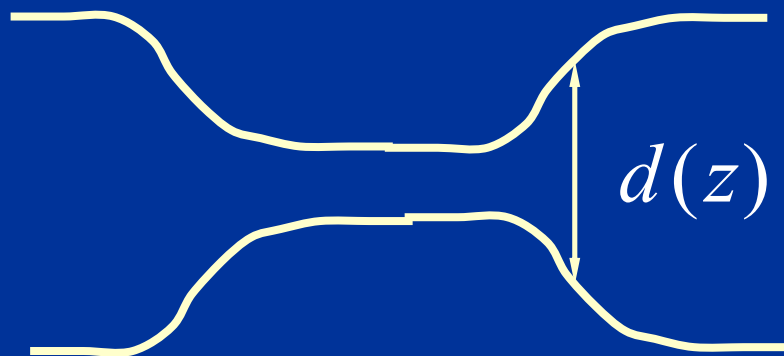
Frequency dependence
of noise

Non-equilibrium effects:
other noise sources

Optics

Decoherence and dephasing

Quantum point contact

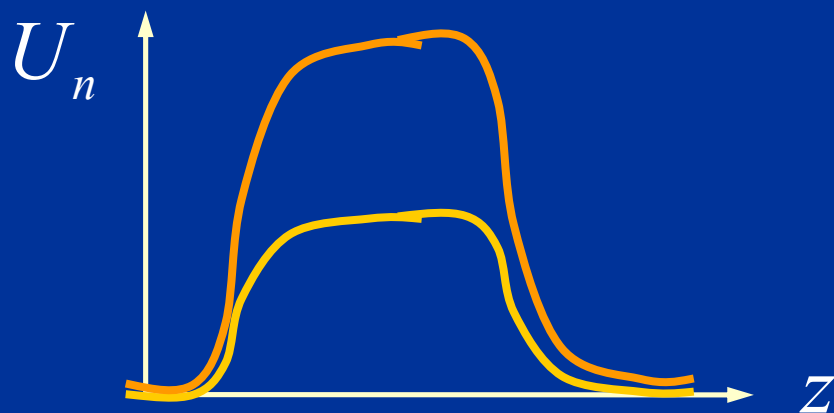


Adiabatic approximation

Glazman, Lesovik,
Khmelnitskii, Shekhter '88

$$E_{\perp} = \frac{\pi^2 n^2 \hbar^2}{2m d^2(z)}$$

serves as an external channel-dependent potential energy



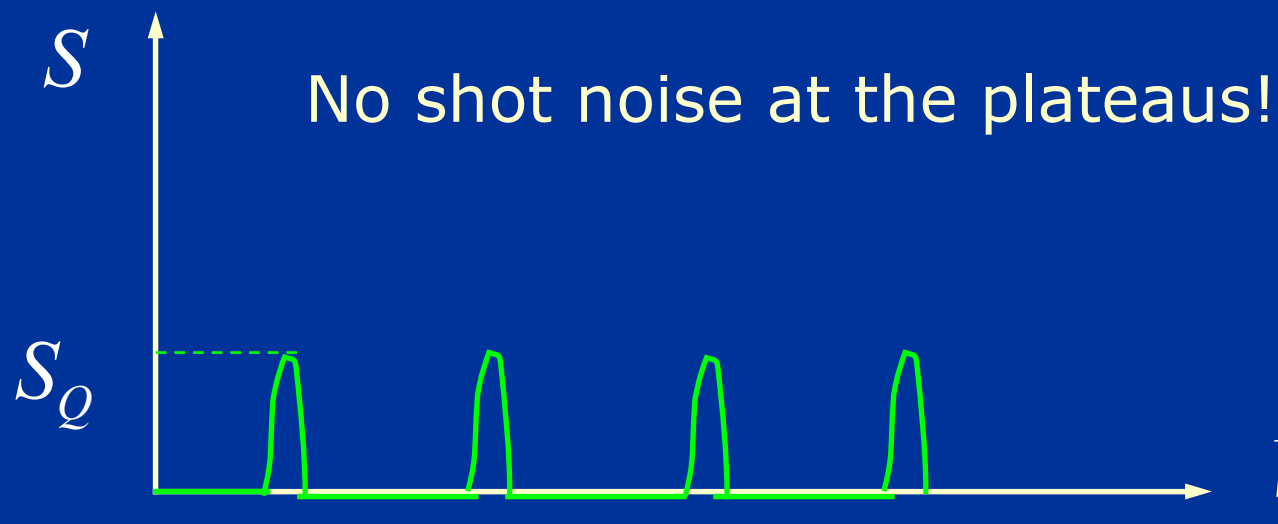
$$T_n = \begin{cases} 0 & E \square U_n^{\max} \\ 1 & E \square U_n^{\max} \end{cases}$$

Quantum point contact

Van Wees *et al* '88
Wharam *et al* '88



$$G_Q = 2s \frac{e^2}{2\pi\hbar}$$



$$S_Q = 2s \frac{e^3 |V|}{4\pi\hbar}$$

Quantum point contact

Reznikov *et al* '95

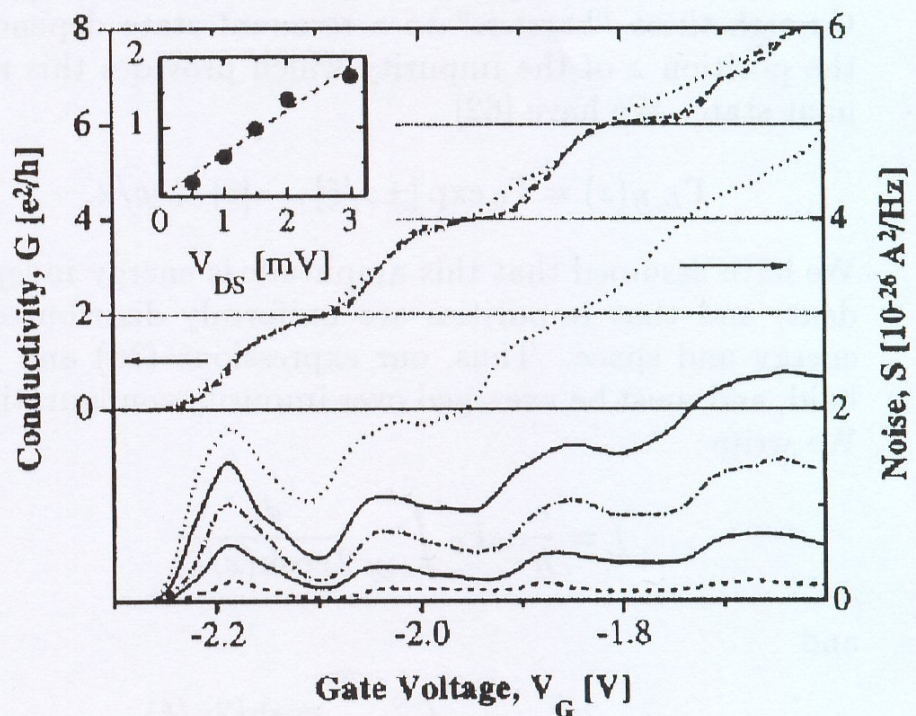
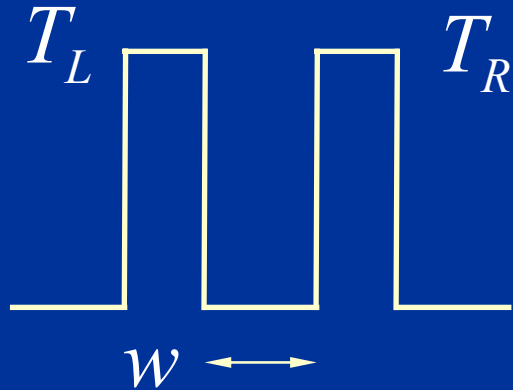


FIG. 7. Conductance (upper plot) and shot noise (lower plot) as functions of the gate voltage, as measured by Reznikov *et al* [42]. Different curves correspond to five different bias voltages.

Double barrier



$$T(E) = \frac{T_L T_R}{1 + R_L R_R - 2\sqrt{R_L R_R} \cos \theta(E)}$$

$$\theta(E) = 2w\sqrt{2mE} / \hbar$$

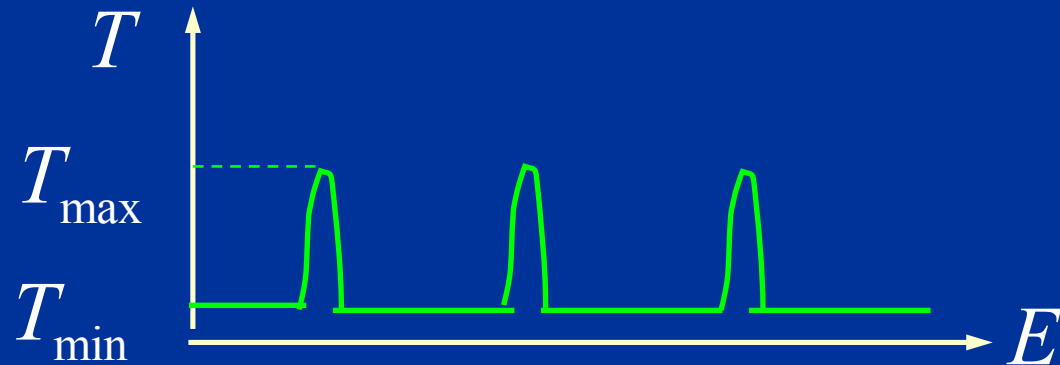
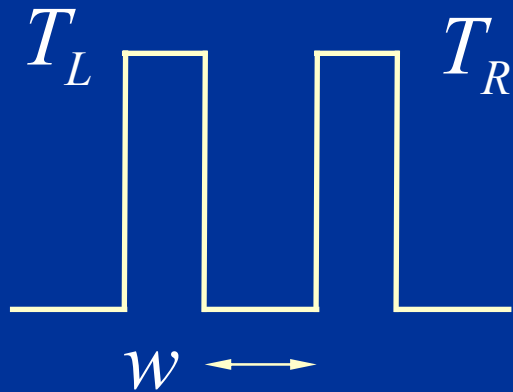
Resonant tunneling

$$\theta(E) = 2\pi n \Rightarrow T = T_{\max} = \frac{4T_L T_R}{(T_L + T_R)^2}$$

$$T_{\min} \propto T_L T_R \ll T_{\max}$$

Sharp resonances in $T(E)$

Double barrier



Linear regime: $T(1-T)$

Non-linear regime: averaging (summation) over energies

Makes a lot of difference!

$$F = \frac{S}{2eI} = \frac{T_L^2 + T_R^2}{(T_L + T_R)^2}$$

$$\frac{1}{2} < F < 1$$

Chen & Ting '91
Büttiker '91
Davies *et al* '92

Double barrier

addressed to Section VII.

Li *et al* '90

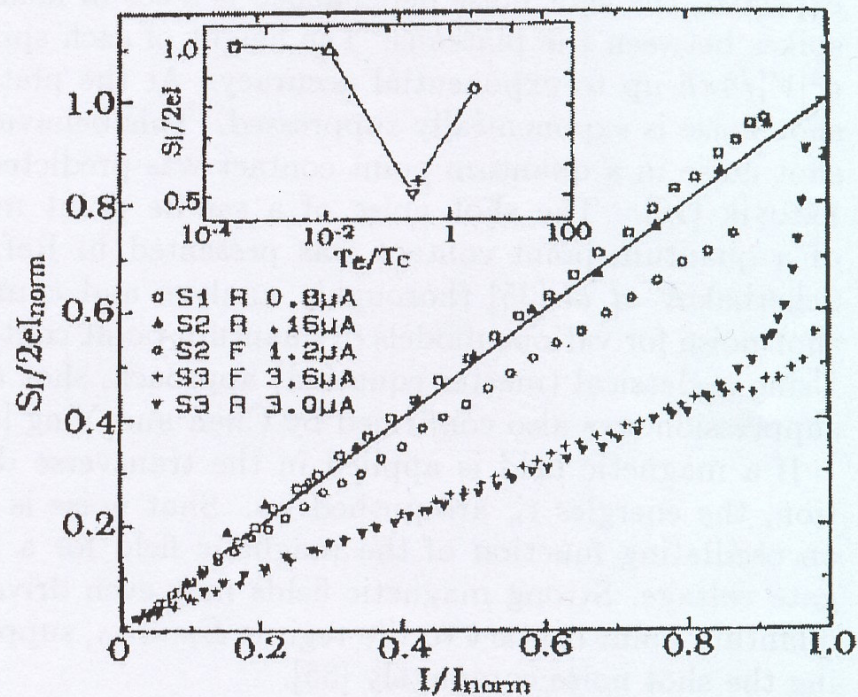
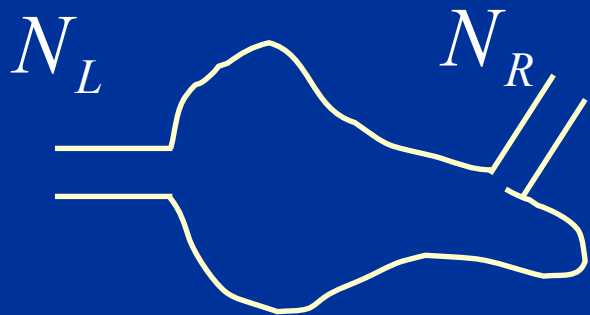


FIG. 9. The Fano factor observed experimentally by Li *et al* [64] as a function of current for three quantum wells, which differ by their asymmetry. The solid line represents the Poisson shot noise value.

Chaotic cavity



Chaotic motion is described by randomness of the scattering matrix:
Random Matrix Theory

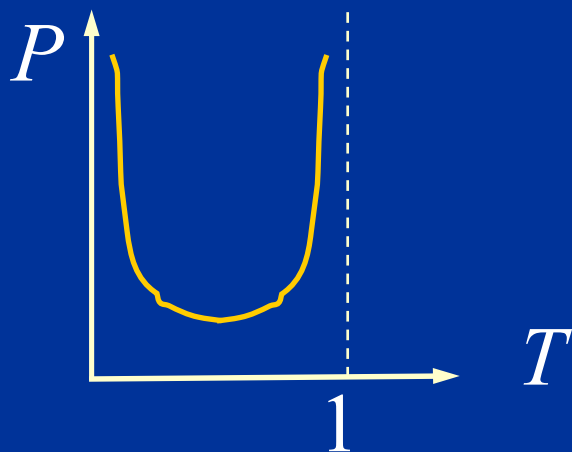
Baranger & Mello '94

Jalabert, Pichard & Beenakker '94

Describe as 2 QPC in series: Nazarov '95

Symmetric, $N_L = N_R$

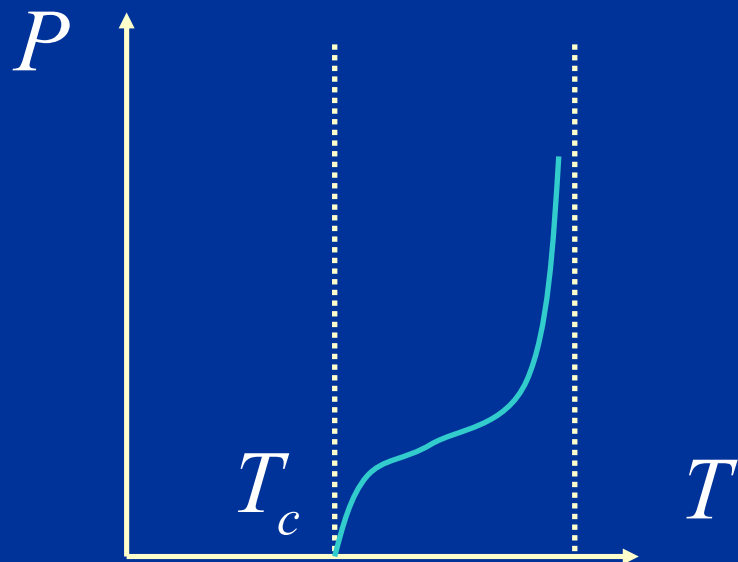
Distribution function:



$$P(T) = \frac{1}{\pi \sqrt{T(1-T)}}$$

Chaotic cavity

General case: $N_L \neq N_R$



$$P(T) = \frac{N_L + N_R}{2\pi G_Q} \frac{1}{T} \sqrt{\frac{T - T_c}{1 - T}}$$

$$T_c = \frac{(N_L - N_R)^2}{(N_L + N_R)^2}$$

Fano factor:

$$F = \frac{N_L N_R}{(N_L + N_R)^2}$$

Conductance:

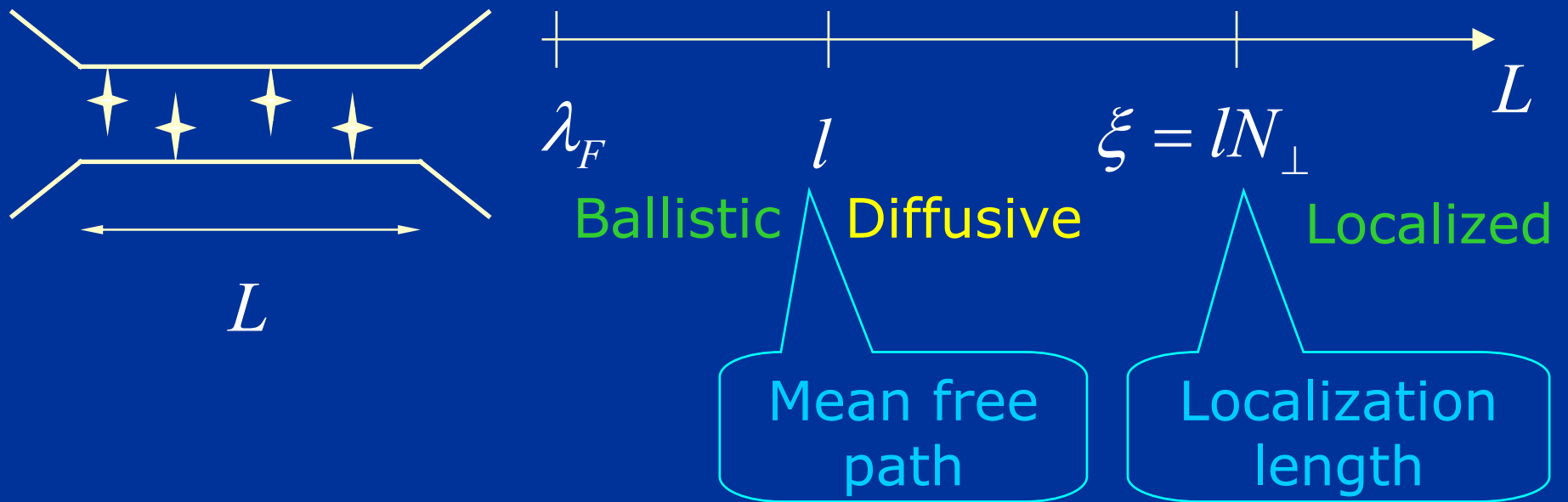
$$G = G_Q \frac{N_L N_R}{N_L + N_R}$$

Ohm's law!

Exp: Oberholzer *et al* '01

Universal!

Metallic diffusive wire

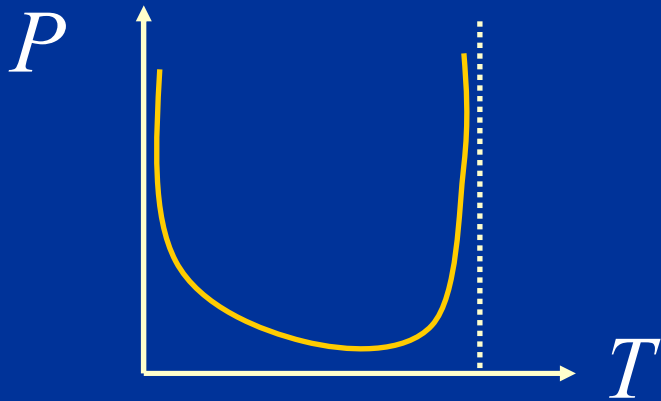


Transmission eigenvalues are random quantities.

$$\langle T \rangle = \frac{l}{L} \ll 1$$

Transmission distribution??

Metallic diffusive wire



$$P(T) = \frac{l}{2L} \frac{1}{T\sqrt{1-T}}$$

Bimodal!

Fano factor:

$$F = \frac{1}{3}$$

Universal!

Beenakker & Büttiker '92
Nagaev '92

Metallic diffusive wire

Henny *et al* '99

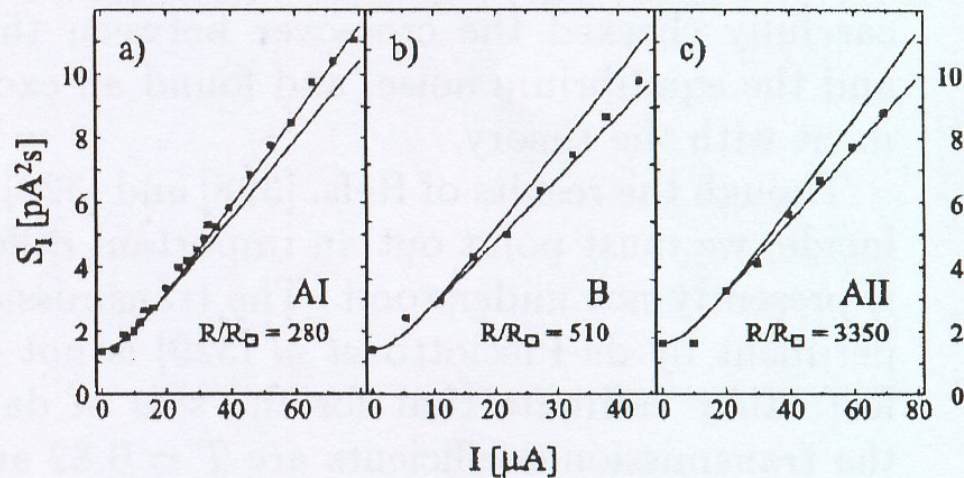
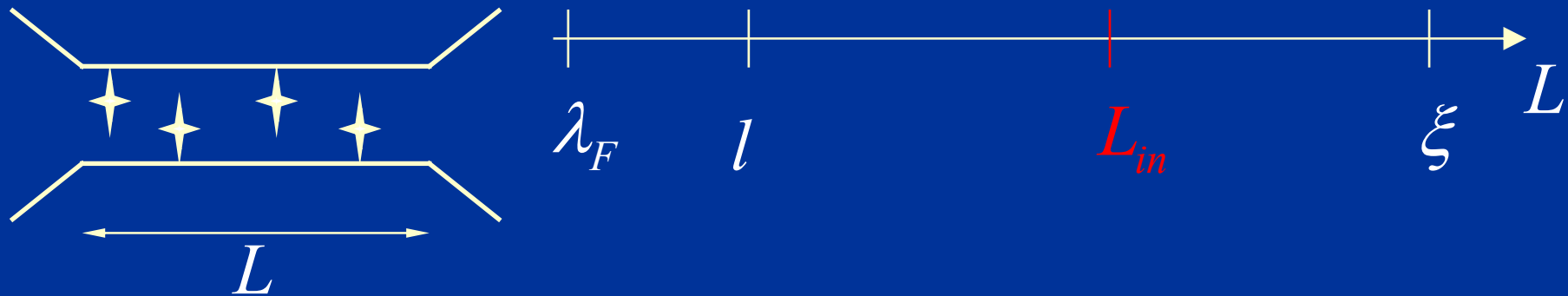


FIG. 11. Shot noise measurements by Henny *et al* [81] on three different samples. The lower solid line is $1/3$ -suppression, the upper line is the hot-electron result $F = \sqrt{3}/4$ (see Section VI). The samples (b) and (c) are short, and clearly display $1/3$ -suppression. The sample (a) is longer (has lower resistance), and the shot noise deviates from the non-interacting suppression value due to inelastic processes.

Inelastic scattering



- Decoherence: no energy exchange, only the phase of the wave function is modified. No effect on noise. Double-step distribution.
- Electron heating: energy is exchanged within electron system.
- Inelastic scattering: energy is transferred to *e.g.* phonons. Equilibrium (Fermi) distribution.

Boltzmann-Langevin equation

Results for shot noise like $F=1/3$ seem to be classical.
Can they be obtained classically?

Boltzmann equation:
$$\left(\partial_t + v \nabla + eE \partial_p \right) f = I[f]$$

Collision integral:

$$I[f_p] = \sum_{p'} [J(p', p, r, t) - J(p, p', r, t)]$$
$$J(p, p', r, t) = W(p, p', r) f_p (1 - f_{p'})$$

W – scattering probability per unit time

Boltzmann-Langevin equation

Add the fluctuating part to the elementary currents J :

$$\begin{aligned} J &= \langle J \rangle + \delta J, \quad \langle \delta J \rangle = 0 \\ \langle \delta J(p_1 p_2 r t) \delta J(p'_1 p'_2 r' t') \rangle \\ &= \delta_{p_1 p'_1} \delta_{p_2 p'_2} \delta(r - r') \delta(t - t') \langle J(p_1 p_2 r t) \rangle \end{aligned}$$

Results in Langevin sources in Boltzmann equation:

$$\left(\partial_t + v \nabla + e E \partial_p \right) f = I[f] + \xi(p, r, t)$$

$$\langle \xi \rangle = 0, \quad \langle \xi(r p t) \xi(r' p' t') \rangle \propto \delta(r - r') \delta(t - t')$$

Metallic diffusive wires

Diffusion approximation:

- Weak dependence of the direction \vec{n} of momentum
- Sharp dependence on energy

$$f = f_0 + \vec{n} \vec{f}_1$$

Result:

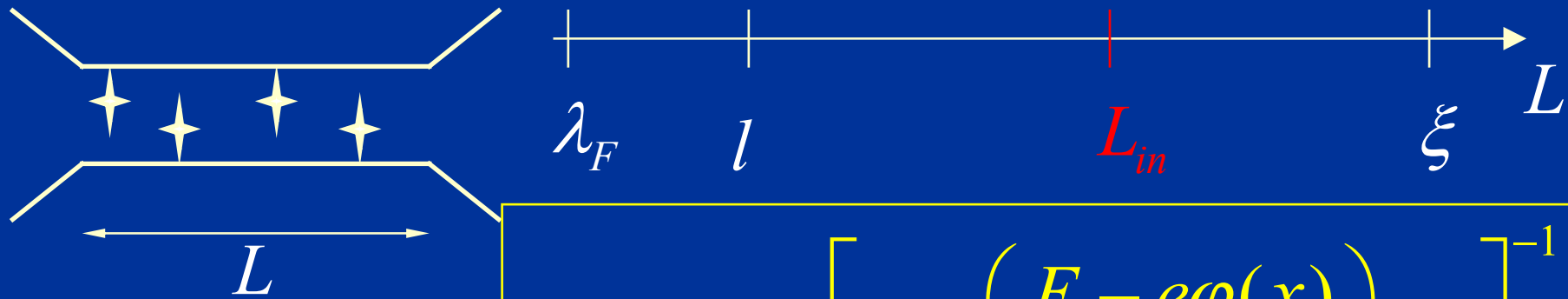
$$S = 4\sigma \int dE dx f(x, E) [1 - f(x, E)]$$

$$\nabla^2 f = 0$$

Gives

$$F = 1/3$$

Electron heating



Ansatz:

$$f(E, x) = \left[\exp\left(\frac{E - e\varphi(x)}{k_B T(x)}\right) + 1 \right]^{-1}$$

Equilibrium at local temperature

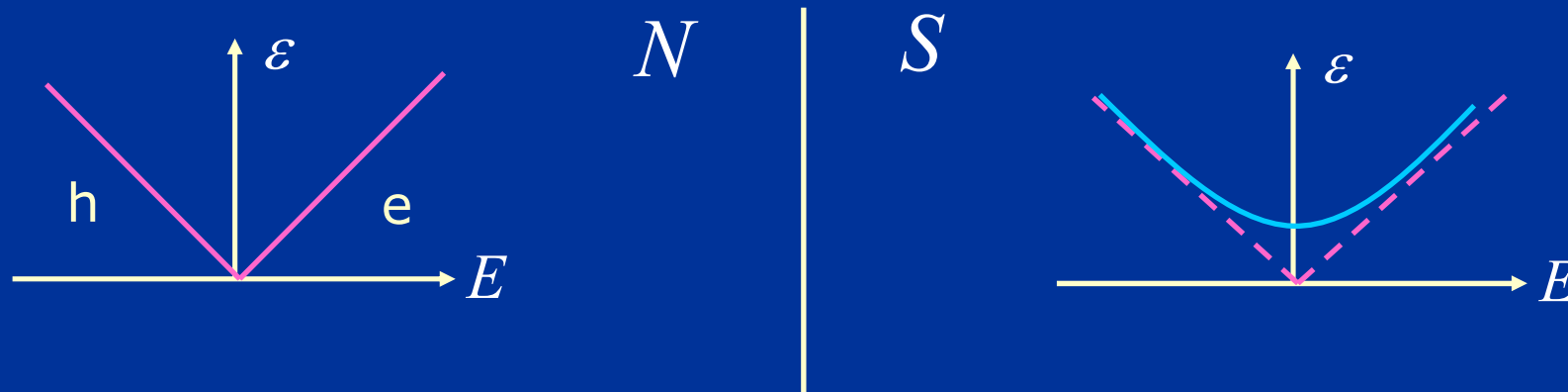
Energy conservation:

$$T(x) = \sqrt{T_0^2 + \frac{3}{k_B^2 \pi^2} \left(\frac{eV}{L}\right)^2 x(L-x)}$$

Fano factor: $F = \frac{\sqrt{3}}{4} \approx 0.43$

Nagaev '95; Kozub & Rudin '95

Andreev reflection



For voltages $e|V| < \Delta$ - no normal transport

Andreev reflection: An electron is reflected back from the interface as a hole

- ✓ Energy: conserved
- ✓ Momentum: (always) conserved; velocity changes sign
- ✓ Charge: **not conserved!** Charge deficit $2e$ – a Cooper pair

Andreev reflection



Khlus '87
De Jong & Beenakker '94
Martin '96

$$G = G_Q \sum_p \frac{2T_p^2}{(2 - T_p)^2}$$

$$S = 32e|V|G_Q \sum_p \frac{T_p^2(1 - T_p)}{(2 - T_p)^4}$$

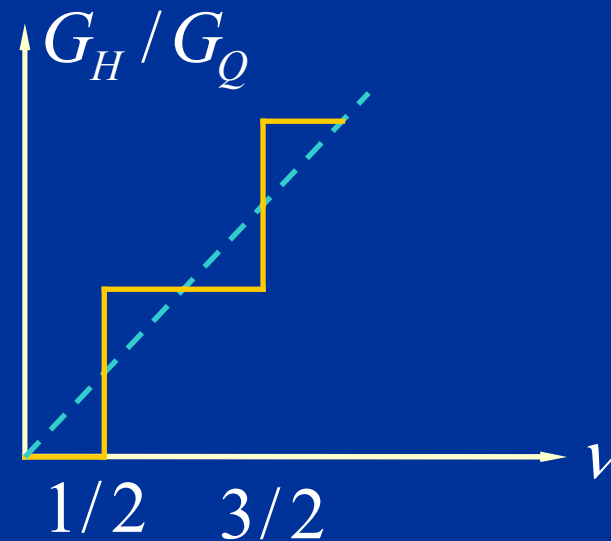
Tunnel junction:

$$G = \frac{G_Q}{2} \sum_p T_p^2$$

$F = 2$: Transfer of double charge!

Quantum Hall edge states

A nanostructure in a strong (quantizing) magnetic field



Integer QHE: transport only via edge states.

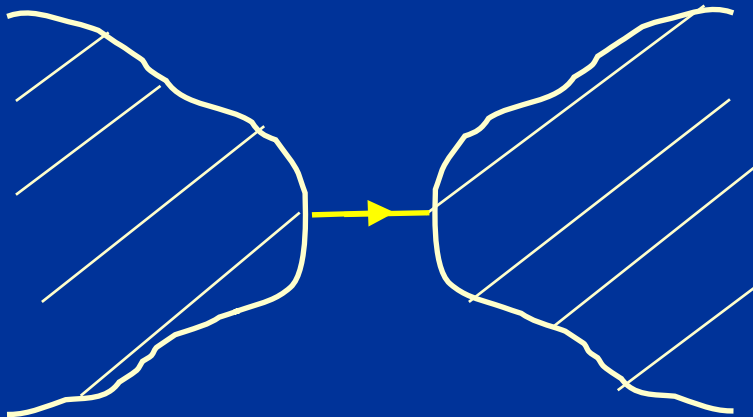
Fractional QHE: additional steps at $\nu = p/q$

New state of matter – strongly correlated system

Quasiparticles: fractional charge and fractional statistics

Quantum Hall edge states

High barrier



Kane & Fisher '94

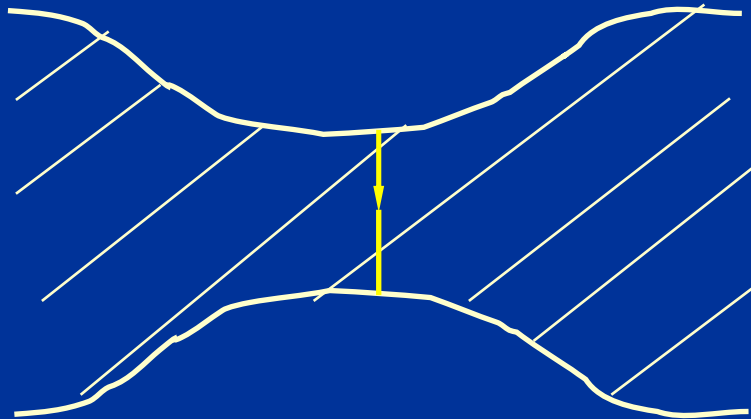
De Chamon, Freed, & Wen '96

Transmission is due to the tunneling of electrons between edge states

Ordinary shot noise of a tunnel barrier

Quantum Hall edge states

Low barrier



Kane & Fisher '94

De Chamon, Freed, & Wen '96

Backscattering is due to the tunneling of quasiparticles between edge states

Effective charge: seen in shot noise!

$$e_{\text{eff}} = e/q$$

Quantum Hall edge states

Saminadayar *et al* '99

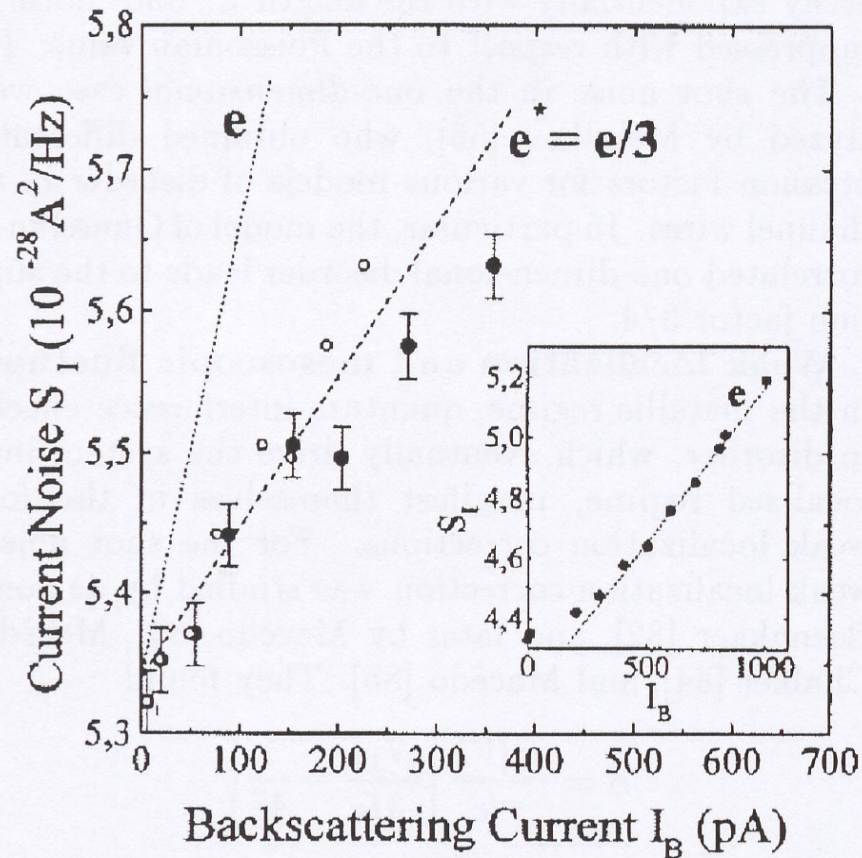


FIG. 38. Experimental results of Saminadayar *et al* [328] for $\nu = 1/3$ (strong tunneling - weak backscattering regime).